RF

Notice of Allowability	Application No.	Applicant(s)	
	10/001,785	YAMAZAKI ET AL.	
	Examiner	Art Unit	
	Craig A. Thompson	2813	
The MAILING DATE of this communication apperall claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RI	(OR REMAINS) CLOSED in or other appropriate comm GHTS. This application is	n this application. If not included unication will be mailed in due could	rse. THIS
 This communication is responsive to <u>communication of 7/2</u> The allowed claim(s) is/are <u>1-103</u>. The drawings filed on <u>05 December 2001</u> are accepted by Acknowledgment is made of a claim for foreign priority una)	the Examiner. der 35 U.S.C. § 119(a)-(d)	or (f).	
 Certified copies of the priority documents have 			
2. Certified copies of the priority documents have	• •		
Copies of the certified copies of the priority do	cuments have been receive	d in this national stage application	from the
International Bureau (PCT Rule 17.2(a)).			
* Certified copies not received: 5. Acknowledgment is made of a claim for domestic priority ur reference was included in the first sentence of the specifical			pecific
(a) \square The translation of the foreign language provisional a	pplication has been receive	d.	
 Acknowledgment is made of a claim for domestic priority ur in the first sentence of the specification or in an Application 		or 121 since a specific reference w	as included
Applicant has THREE MONTHS FROM THE "MAILING DATE" of below. Failure to timely comply will result in ABANDONMENT of	this communication to file this application. THIS THE	a reply complying with the requirem REE-MONTH PERIOD IS NOT EXT	nents noted FENDABLE.
 A SUBSTITUTE OATH OR DECLARATION must be subm INFORMAL PATENT APPLICATION (PTO-152) which give 	itted. Note the attached EX es reason(s) why the oath o	AMINER'S AMENDMENT or NOTI r declaration is deficient.	CE OF
 8. CORRECTED DRAWINGS (as "replacement sheets") mus (a) including changes required by the Notice of Draftspers 1) hereto or 2) to Paper No (b) including changes required by the proposed drawing company. 	on's Patent Drawing Revie	ch has been approved by the Exam	
(c) ☐ including changes required by the attached Examiner's	s Amendment / Comment o	r in the Office action of Paper No.	·
Identifying indicia such as the application number (see 37 CFR 1 each sheet. Replacement sheet(s) should be labeled as such in the			:k) of
 DEPOSIT OF and/or INFORMATION about the depo- attached Examiner's comment regarding REQUIREMENT FOR T 	sit of BIOLOGICAL MAT HE DEPOSIT OF BIOLOG	ERIAL must be submitted. Note ICAL MATERIAL.	the
Attachm nt(s)			
1⊠ Notice of References Cited (PTO-892)	5 ☐ Notice of Inf	ormal Patent Application (PTO-152	2)
 2☐ Notice of Draftperson's Patent Drawing Review (PTO-948) 3☒ Information Disclosure Statements (PTO-1449 or PTO/SB/08) Paper No 	6☐ Interview Su	mmary (PTO-413), Paper No	_·
	- Zarimers	Amendment/Comment	
4 Examiner's Comment Regarding Requirement for Deposit of Biological Material	8⊠ Examiner's 9⊡ Other	Statement of Reasons for Allowand .	Эe
		Craig A. Thompson Primary Examiner Art Unit: 2813	

An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

The application has been amended as follows:

• In claim 7, specification page 56, line 4: "source in a range of is 1 to 40" has been replaced with - - source is in a range of 1 to 40 - -.

The amendment is considered to be a correction of a typographical error and not to affect the scope of the claim.

REASONS FOR ALLOWANCE

The following is an examiner's statement of reasons for allowance: prior art of record does not describe or suggest applicants' invention set froth in claim 1 (and dependent claims 3, 5, 6, 20, 21, 22, 23, 24, 25, 26, 27, and 35) a method for making a semiconductor device wherein an amorphous semiconductor film is formed on an insulating surface, a catalytic element is added to the amorphous semiconductor film, and the amorphous film is crystallized by a controlled light source to irradiate with a pulsed light to form a crystalline semiconductor film. Similarly, prior art of record does not describe or suggest the invention of claim 2 (and dependent claims 36-47) wherein

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the light emitting time of the light source is in a range of 1 to 60 seconds. Prior art of record does not describe or suggest the invention of claim 6 (and dependent claims 8-10, 15, 16, 52-60 and further dependent claims 17, 11, 18, 49, 19, 48, 50 and 51) wherein an impurity element is added to the crystalline semiconductor film and the catalytic element is gettered by the irradiation with pulsed light, in the context of the recited process.

Prior art of record does not describe or suggest applicants' invention set forth in claim 7 (and dependent claims 61-82) wherein the catalytic element is gettered by irradiating with the light and the light emitting time of the light source is in the range of 1 to 40 seconds. Prior art of record does not describe or suggest the invention of claim 12 (and dependent claims 13-14, and 83-97) wherein the catalytic element is added to a first amorphous film, the film is heated to crystallize it, a second amorphous film is formed on the crystalline semiconductor film and impurity is added to the second amorphous film and the catalytic element is gettered to the second amorphous film my controlling a light source to irradiate with pulsed light, in the context of the recited processes.

Prior art of record does not describe or suggest applicants' invention set forth in claim 28 (and dependent claims 31-34 and 98) wherein an amorphous semiconductor film is formed on an insulating surface, a catalytic element is added to a surface of the of the amorphous film, the amorphous film is crystallized by controlling a light source to irradiate a pulsed light, an impurity is added to the crystalline film, and the catalytic element is gettered by controlling the light source to irradiate with pulsed light, in the

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context of the recited processes. Finally, prior art of record does not describe or suggest applicants' invention set forth in claim 29 (and dependent claims 30, and 99-103) wherein the catalytic element is gettered and gate formation steps are carried out, in the context of the recited processes.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Cited Prior Art

The prior art made of record and not relied upon is considered pertinent to applicant's disclosure. Funnai et al. (U.S. Patent No. 6,162,667) teaches a method for making TFTs wherein an amorphous film is formed and a catalyst is added uniformly and in very low concentration (abstract) and columns 3-4) Crowder et al. (IEEE 1998 article) teaches forming Silicon TFTs using excimer laser crystallization (page 306). Gadnoczi et al. (J. Applyied Physics 1991 article) teaches crystallization of amorphous Si using aluminum and annealing in argon from 400 to 1000K (page 6394).

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Conclusion

Any inquiry concerning this communication or earlier communications from the

examiner should be directed to Craig A. Thompson whose telephone number is

(703)305-4789. The examiner can normally be reached on Monday-Friday 8:00 am -

4:30 pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's

supervisor, Carl Whitehead, Jr. can be reached on (703)308-4940. The fax phone

number for the organization where this application or proceeding is assigned is

(703)872-9318.

Any inquiry of a general nature or relating to the status of this application or

proceeding should be directed to the receptionist whose telephone number is (703)308-

0956.

Craig A. Thompson
Primary Examiner

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